

#### ABSTRACT OF DISCLOSURE

Each memory cell is constituted by a pair of magnetic memory elements. The magnetic memory elements are connected at one  
5 ends to sense bit lines, and at the other ends to a sense word line through a pair of reverse current preventing diodes, respectively. A constant current circuit is disposed on the grounded side of the sense word line. The constant current circuit has a function of fixing a current flowing through the  
10 sense word line, and is constituted by a constant voltage generating diode, a transistor and a current limiting resistor.

[Selected Drawing] Fig. 2